

650V Super-Junction Power MOSFET

FEATURES

- Very low FOM R_{DS(on)}×Q_g
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

TO-220 GD 5	TO-220F GDS	T0-251 G D S	TO-252
RoHS	TO-262 GDS	TO-263 GDS	

Device Marking and Package Information						
Device	TPP65R940C	TPA65R940C	TPU65R940C	TPD65R940C	TPC65R940C	TPB65R940C
Package	TO-220	TO-220F	TO-251	TO-252	TO-262	TO-263
Marking	65R940C	65R940C	65R940C	65R940C	65R940C	65R940C

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter	Cumhal	Value			
Farameter	Symbol	TO-251, TO-252	TO-220F	Unit	
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	650		V	
Continuous Drain Current	I _D	4		А	
Pulsed Drain Current (note1)	I _{DM}	12		А	
Gate-Source Voltage	V _{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	52.8		mJ	
Avalanche Current (note1)	I _{AR}	0.8		А	
Repetitive Avalanche Energy (note1)	E _{AR}	0.09		mJ	
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	28	23	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance					
Devementer	Symbol	Value	l luit		
Parameter	Symbol	TO-251, TO-252	TO-220F	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	4.4	5.5	°C/W	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62	80	°C/W	

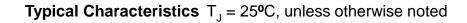


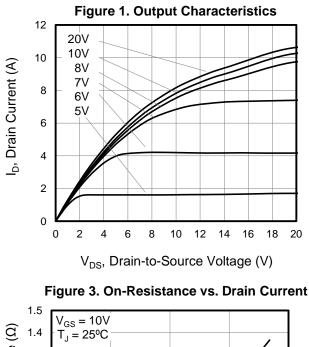
Specifications $T_J = 25^{\circ}C$, ur	less othe	rwise noted					
Parameter	Symbol	Test Conditions	Value			Unit	
Turumeter	Cymbol		Min.	Тур.	Max.		
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_{D} = 250\mu A$	650			V	
Zara Cata Valtaga Drain Currant		$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100		
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.0	V	
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 1A		0.88	1.0	Ω	
Forward Transconductance (Note3)	g _{fs}	V _{DS} = 10V, I _D = 1A		3		S	
Dynamic				•			
Input Capacitance	C _{iss}			350			
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$		20		pF	
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		2.6			
Total Gate Charge	Q _g			7		nC	
Gate-Source Charge	Q _{gs}	$V_{DD} = 520V, I_D = 4A, V_{GS} = 10V$		1.5			
Gate-Drain Charge	Q _{gd}			2.5			
Turn-on Delay Time	t _{d(on)}			36			
Turn-on Rise Time	t _r	V _{DD} = 400V, I _D = 4A,		27			
Turn-off Delay Time	t _{d(off)}	$R_{\rm G} = 25\Omega$		79		ns	
Turn-off Fall Time	t _f			29			
Drain-Source Body Diode Characteri	stics						
Continuous Body Diode Current	I _s	T 0700			3.9		
Pulsed Diode Forward Current	I _{SM}	$T_{\rm C} = 25^{\circ}{\rm C}$			12	A	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 4A, V _{GS} = 0V		0.9	1.2	V	
Reverse Recovery Time	t _{rr}			220		ns	
Reverse Recovery Charge	Q _{rr}	$V_R = 480V, I_F = I_S,$ $di_F/dt = 100A/\mu s$		0.9		μC	
Peak Reverse Recovery Current	I _{rrm}			8		А	

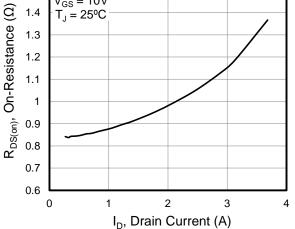
Notes

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. $I_{AS} = 0.8A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 1%

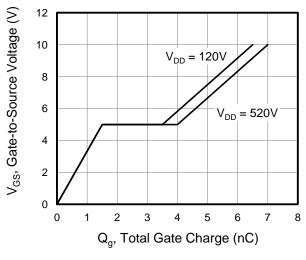


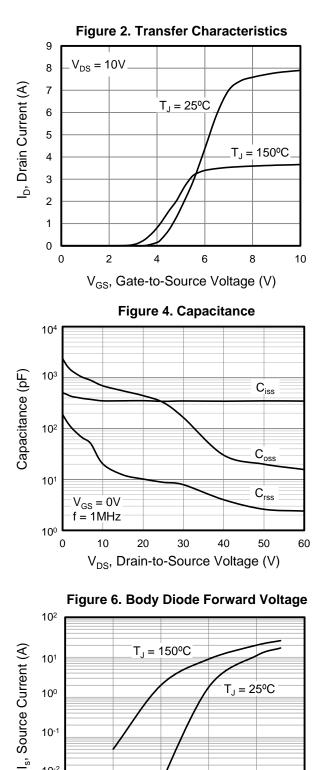












1.2

1

10⁻²

10-3

0.2

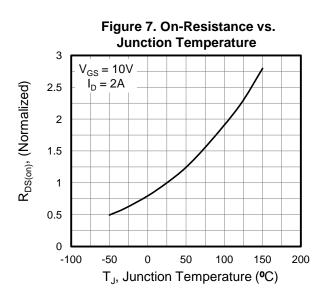
0.4

0.6

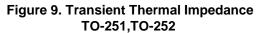
0.8

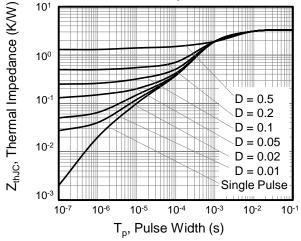
V_{SD}, Source-to-Drain Voltage (V)





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted





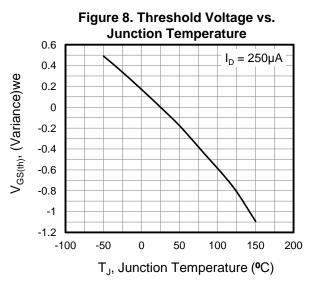
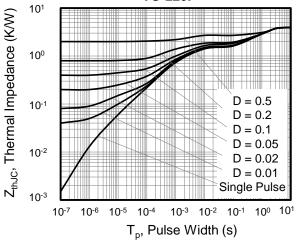
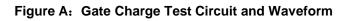


Figure 10. Transient Thermal Impedance TO-220F





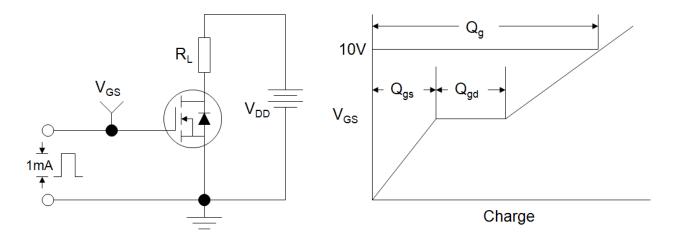


Figure B: Resistive Switching Test Circuit and Waveform

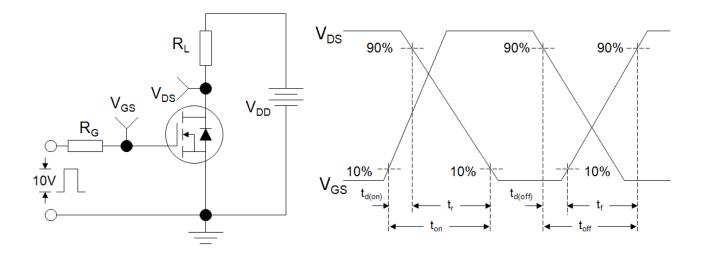
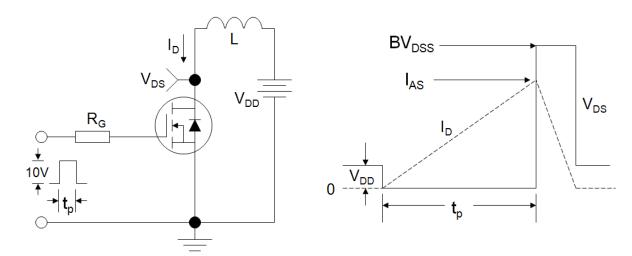
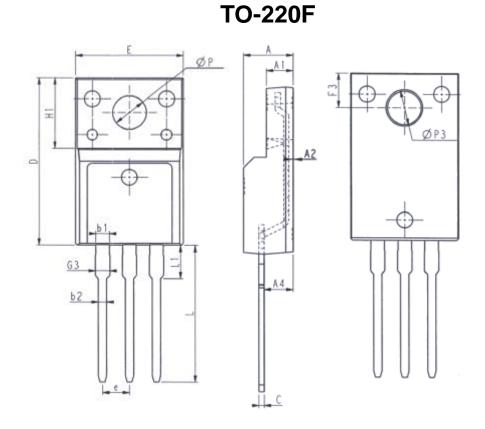


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



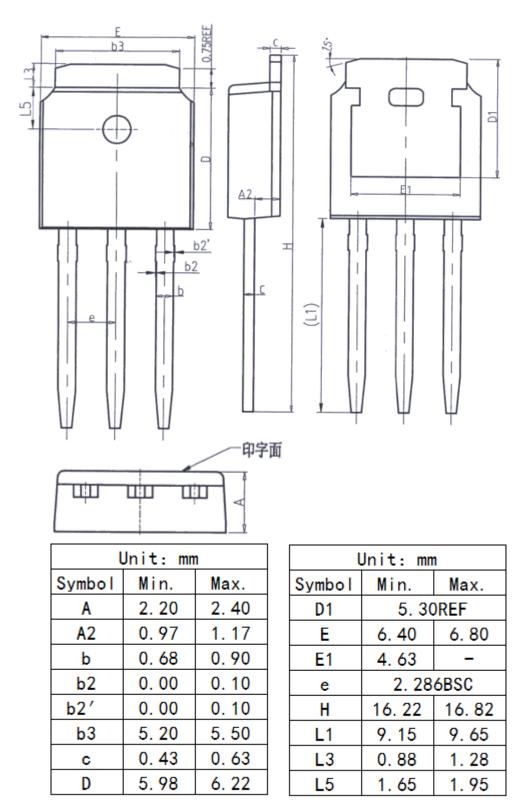




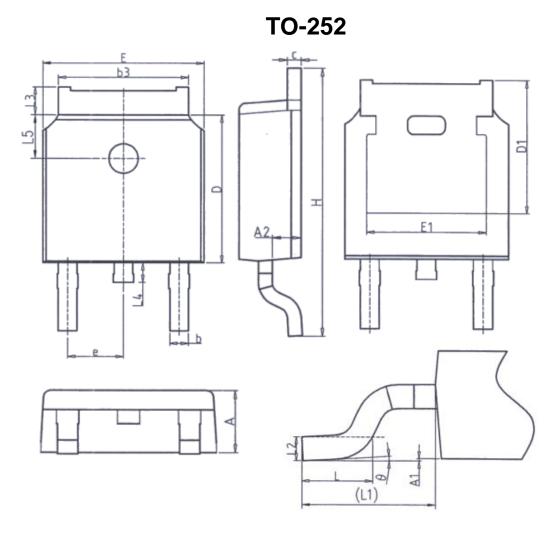
Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13. 28
Α	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	Р	3.03	3.38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
с	0.40	0.65	G3	1.25	1.55
D	15. 57	16. 17	b1	1.18	1.43
H1	6. 70REF		b2	0.70	0.95
e	2. 54BSC				











Unit: mm				
Symbol	Min.	Max.		
A	2.20	2.40		
A1	0.00	0.20		
A2	0.97	1.17		
b	0.68	0.90		
b3	5.20	5.50		
с	0.43	0.63		
D	5.98	6. 22		
D1	D1 5. 30REF			
E	6.40	6.80		
E1	4.63	-		

Unit: mm				
Symbol	Min. Max.			
e	2. 286BSC			
Н	9.40 10.50			
L	1.38 1.75			
L1	2. 90REF			
L2	0, 51	BSC		
L3	0.88 1.28			
L4	-	1.00		
L5	1.65 1.95			
θ	θ 0°			



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